www.vishay.com

Vishay Siliconix

RoHS

COMPLIANT HALOGEN

FREE

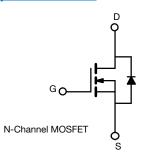
Automotive N-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY						
V _{DS} (V)	60					
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.00200					
I _D (A)	120					
Configuration	Single					
Package	TO-263-7L					

FEATURES

- TrenchFET® power MOSFET
- · Package with low thermal resistance
- 100 % R_g and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ABSOLUTE MAXIMUM RATINGS ($T_c = 25 \degree C$, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-source voltage		V _{DS}	60			
Gate-source voltage		V _{GS}	± 20	V		
Continuous drain current ^a	T _C = 25 °C	ID	120			
Continuous drain current ~	T _C = 125 °C		120			
Continuous source current (diode conduction) ^a	I _S	120	А			
Pulsed drain current ^b	I _{DM}	240				
Single pulse avalanche current	L = 0.1 mH	I _{AS}	75			
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	281	mJ		
Maximum power dissipation ^b	T _C = 25 °C	Р	375	w		
	T _C = 125 °C	P _D	125	vv		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount ^c	R _{thJA}	40	°C/W		
Junction-to-case (drain)		R _{thJC}	0.4	0/11		

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					•			
Drain-source breakdown voltage	V _{DS}	$V_{GS}=0~V,~I_D=250~\mu A$		60	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$		3.0	3.5	v	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$ $V_{DS} = 60 V$		-	-	1		
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	250	μA	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	100	-	-	А	
		V _{GS} = 10 V	I _D = 30 A	-	0.00163	0.00200		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.00300	Ω	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.00360		
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	142	-	S	
Dynamic ^b		•						
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	9100	11 900	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	3550	4700		
Reverse transfer capacitance	C _{rss}			-	160	220		
Total gate charge ^c	Qg	V _{GS} = 10 V V _{DS} = 30 V, I _D = 50 A		-	123	185	nC	
Gate-source charge ^c	Q _{gs}			-	40	-		
Gate-drain charge ^c	Q _{gd}				19	-		
Gate resistance	R _g	f = 1 MHz		4	8.6	13	Ω	
Turn-on delay time ^c	t _{d(on)}			-	48	75		
Rise time ^c	tr	V _{DD} =	= 30 V, R _L = 0.6 Ω	-	26	40		
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 50$ Å, $V_{GEN} = 10$ V, $R_g = 1 \Omega$		-	105	160	ns	
Fall time ^c	t _f			-	25	40		
Source-Drain Diode Ratings and Chara	cteristics ^b	•						
Pulsed current ^a	I _{SM}			-	-	240	А	
Forward voltage	V _{SD}	I _F = 50 A, V _{GS} = 0 V		-	0.84	1.5	V	
Body diode reverse recovery time	t _{rr}	I _F = 25 A, di/dt = 100 A/μs		-	100	200	ns	
Body diode reverse recovery charge	Q _{rr}			-	243	500	nC	
Reverse recovery fall time	t _a			-	48	-		
Reverse recovery rise time	t _b			-	53	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-4.6	-	Α	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

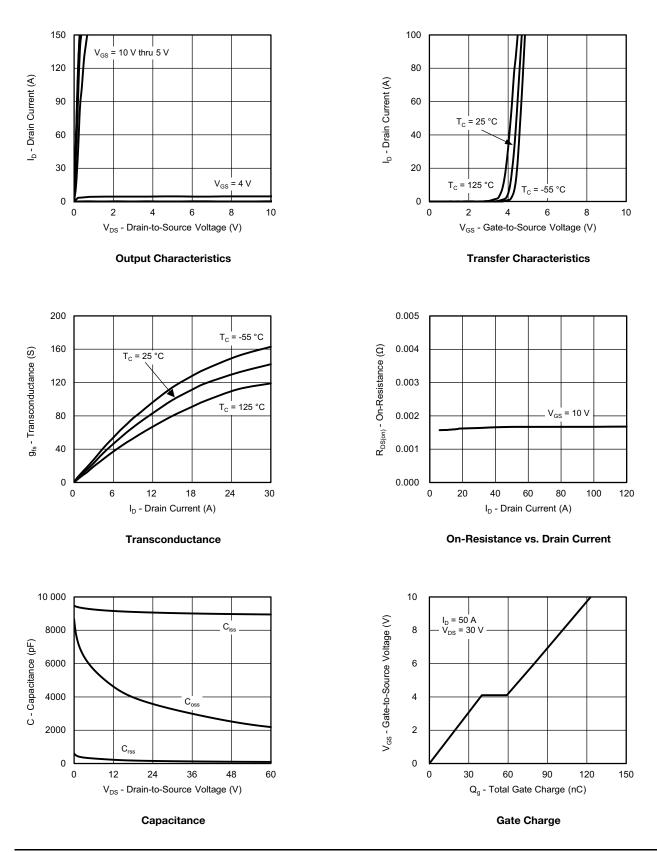
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



Vishay Siliconix

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



S17-0937-Rev. B, 19-Jun-17

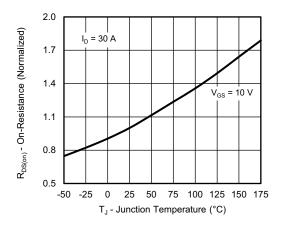
3 tions_contact: automostechsur Document Number: 74738

For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

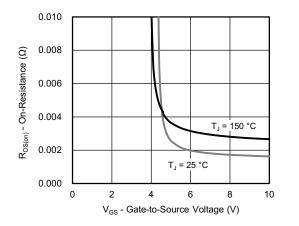


Vishay Siliconix

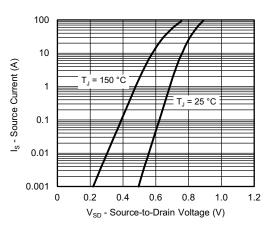
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



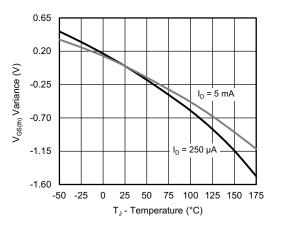
On-Resistance vs. Junction Temperature

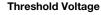


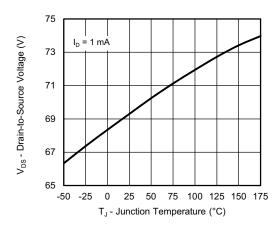
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







Drain Source Breakdown vs. Junction Temperature

For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

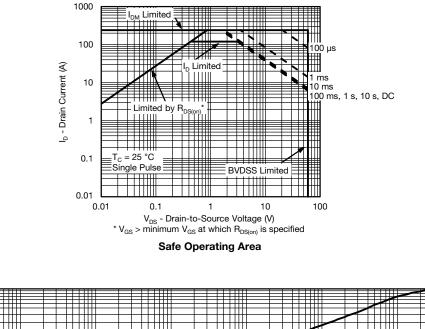


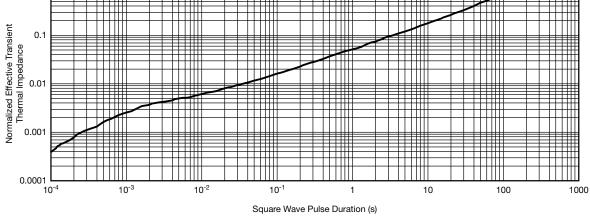
1

SQM50028EM

Vishay Siliconix

THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)





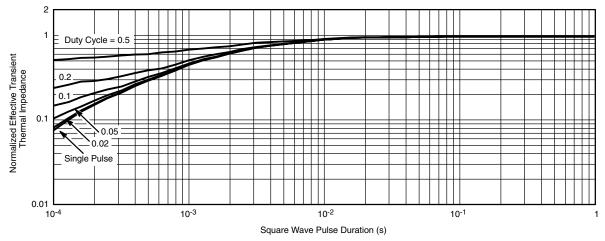
Normalized Thermal Transient Impedance, Junction-to-Ambient



Vishay Siliconix

Document Number: 74738

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

S17-0937-Rev. B, 19-Jun-17

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

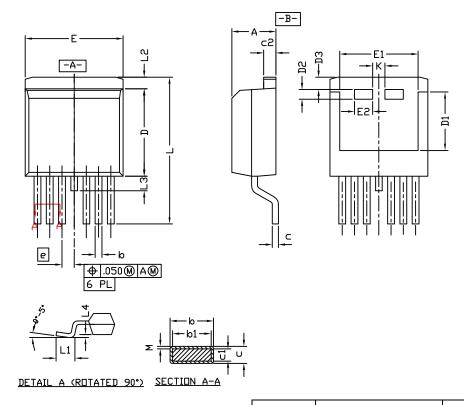
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?74738.



Vishay Siliconix

D²PAK (TO-263-7L) Case Outline



Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin to pin coplanarity max. 4 mils.
- 4. Lead thickness 25 mils.
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils.
- 6. For reference only.
- 7. Use inches as the primary measurement.
- 8. This feature is only for SUM.

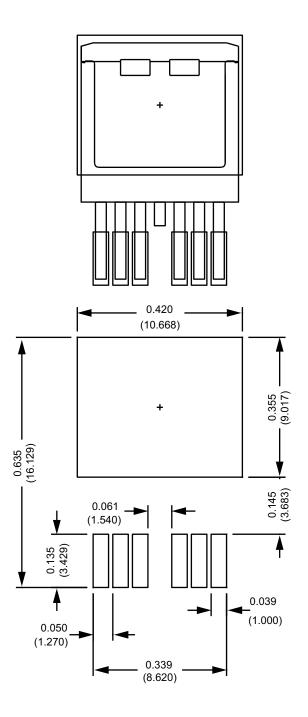
	INC	HES	MILLIMETERS		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c* SUB	0.012	0.018	0.305	0.457	
c* SUM	0.022	0.028	0.559	0.711	
c1	0.018	0.025	0.457	0.635	
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.072	0.078	1.829	1.981	
е	0.050 BSC		1.27 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
М	-	0.002	-	0.050	
ECN: T13-0709-Rev. B, 30-Sep-13 DWG: 6006					





Vishay Siliconix

Recommended Land Pattern D²PAK (TO-263-7L)



Revision: 23-Jul-2020



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.